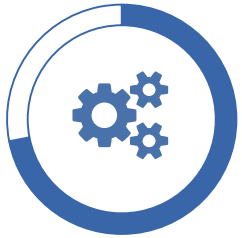






Anisotropic RIE etching supported by a wide range of processes



RIE capabilities over a variety of materials including Silicon compounds, metals, polymers, III-V and II-VI compounds



Modular design approach supporting tiered upgrades



Smaller wafer pieces up to full 200 mm wafer
1x2" to 7x2" ; 1x3" to 3x3" ; 1x4" ; 1x6" ; 1x8"



SYSTEM DESCRIPTION

CORIAL 210RL

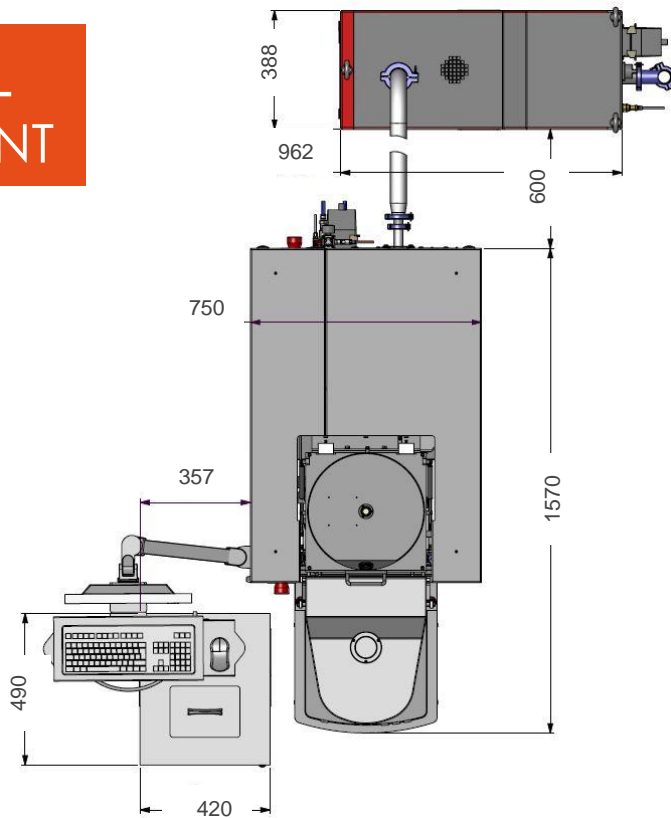


SYSTEM DESCRIPTION

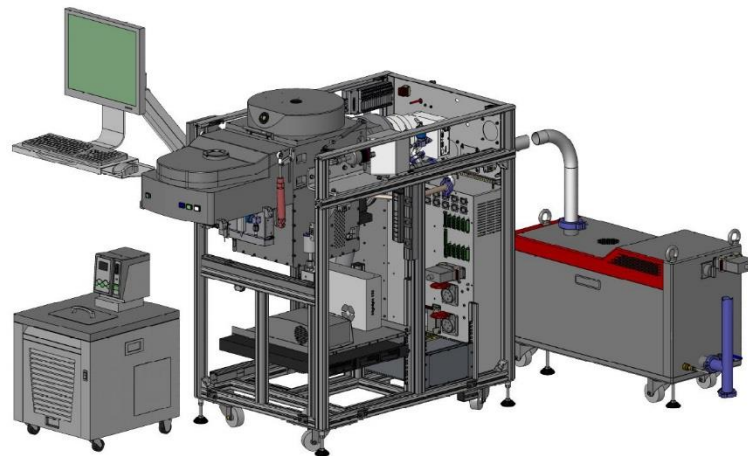
9/5/2018

General View

SMALL
FOOTPRINT



Low CoO

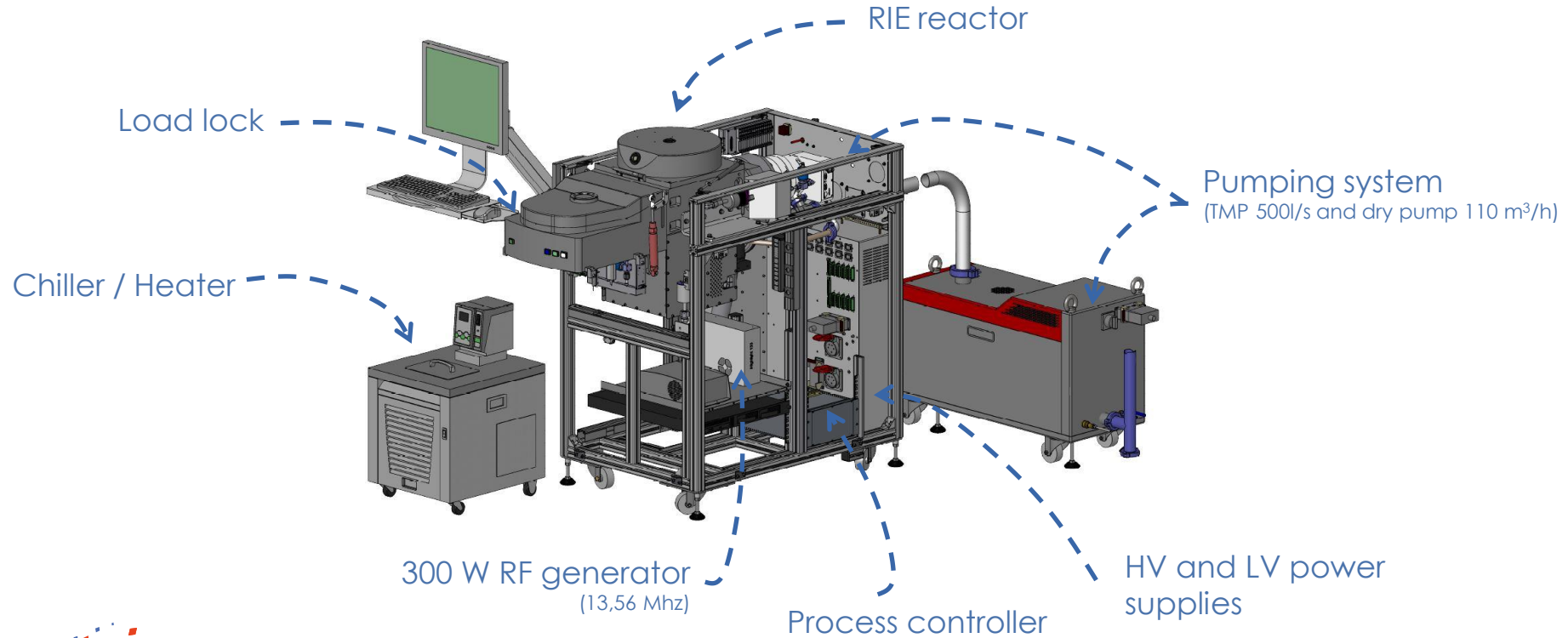




SYSTEM DESCRIPTION

9/5/2018

Detailed View

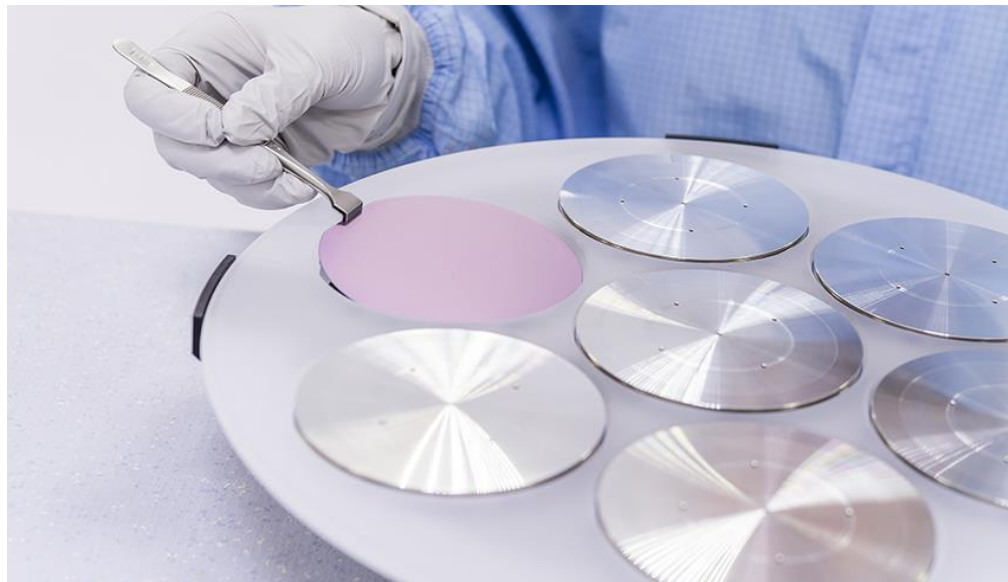




SYSTEM DESCRIPTION

9/5/2018

Loading



< 180 s

LOADING TIME

Vacuum robot

FAST AND REPEATABLE LOAD AND UNLOAD

Shuttle

EASY EXCHANGE BETWEEN SUBSTRATE SHAPE AND SIZE

STANDARD RIE SOURCE **CORIAL 210RL**

RIE SOURCE

Anisotropic RIE Etching

Flexible solution for RIE



1. Load lock enables using a combination of fluorinated and chlorinated chemistries in the same tool
2. Load lock for stable and repeatable process conditions
3. Uniform temperature control for best repeatability
4. Retractable liner for sputter etch increase time between cleans and reduce clean time
5. shuttle (carrier) design, combined with a standard cathode, for a cost-effective and fast reactor adaptation, suitable for multiple applications and substrate types
6. System can be upgraded from a basic RIE tool to an advanced ICP-RIE system

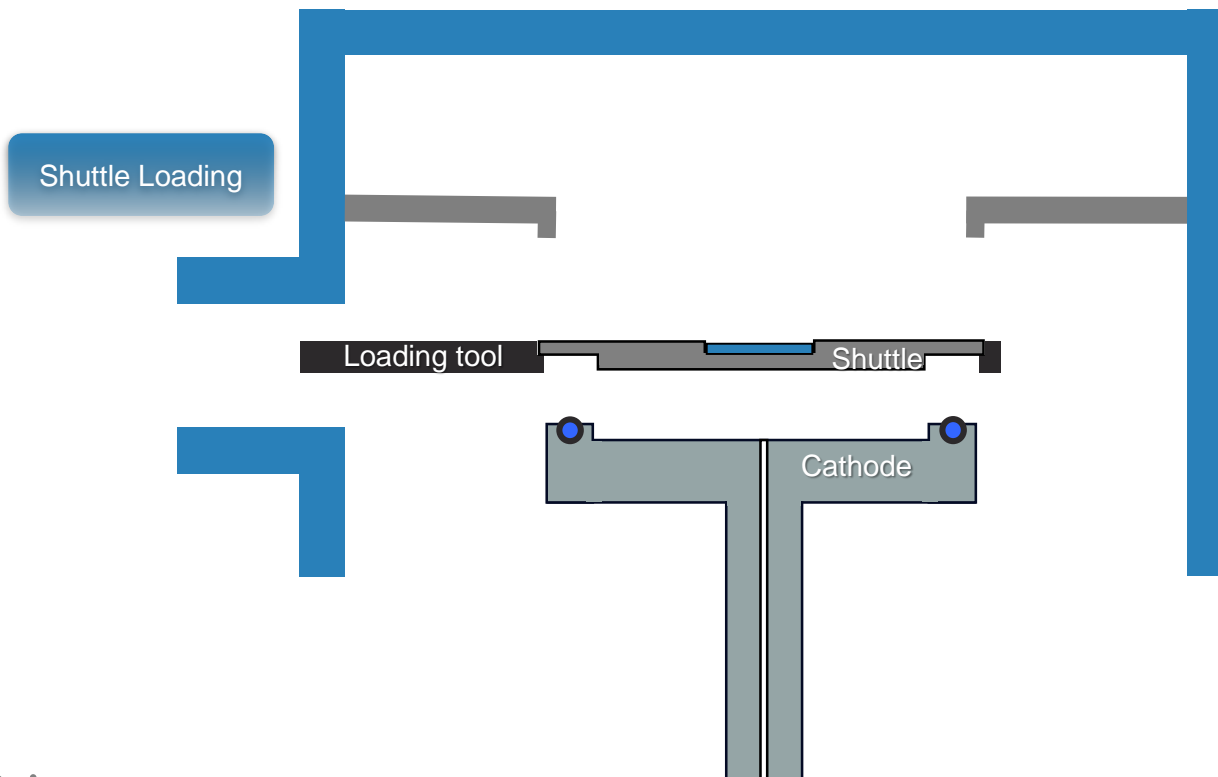
SiO₂ 50 nm/min
Al 250 nm/min
GaAs 300 nm/min



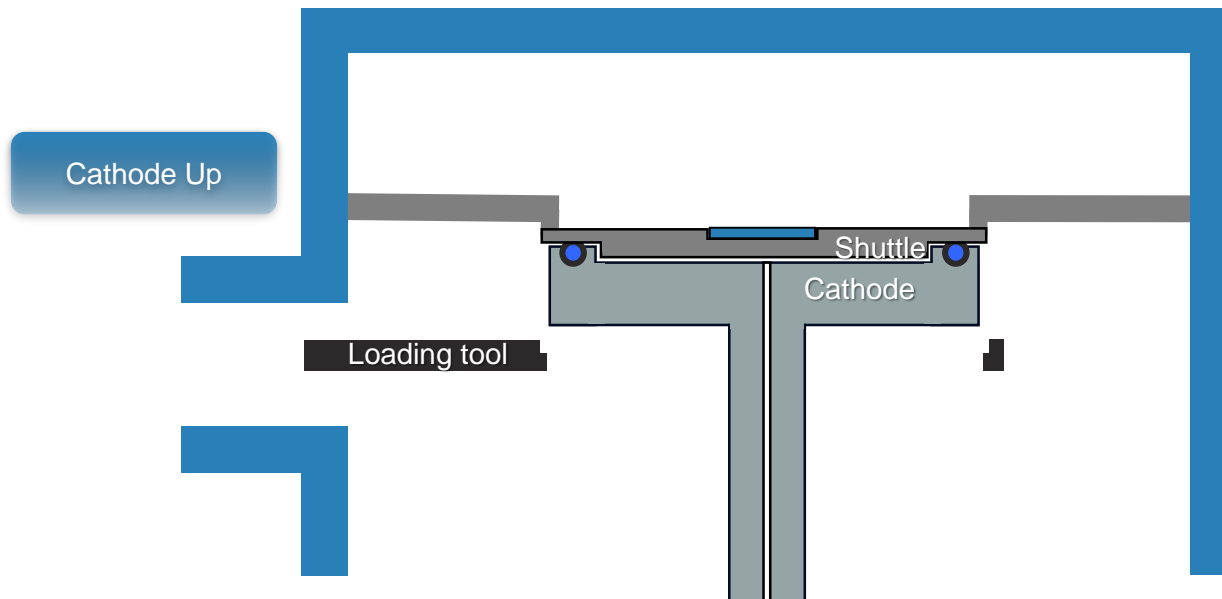
RIE SOURCE

9/5/2018

Operation Sequence



Operation Sequence



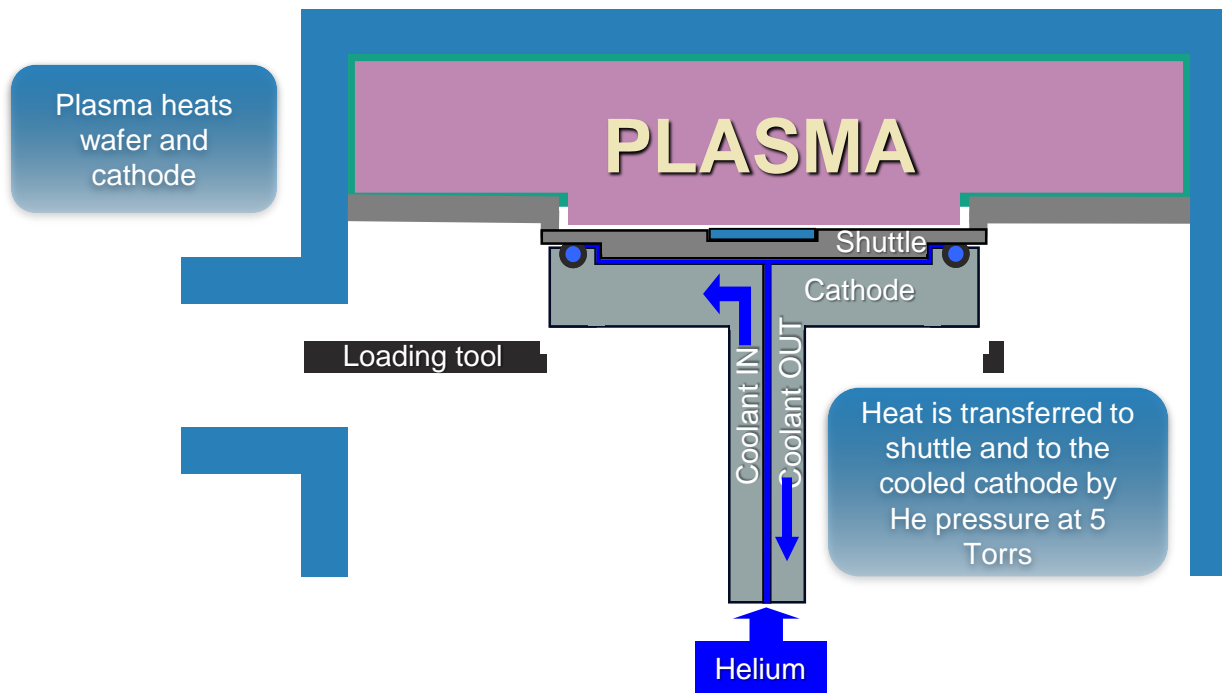
2



RIE SOURCE

9/5/2018

Operation Sequence

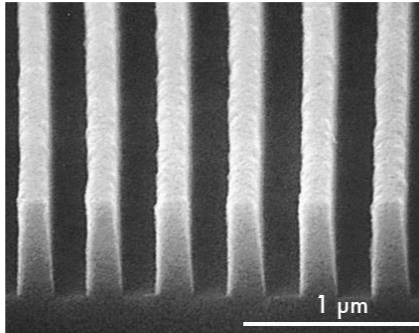


3

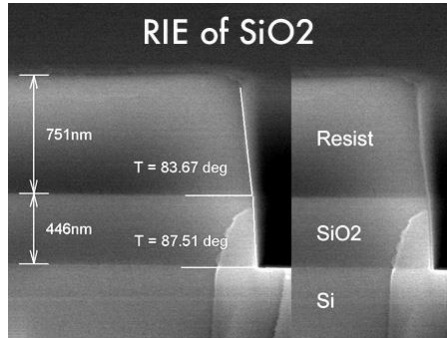
PERFORMANCES RIE PROCESSES **CORIAL 210RL**



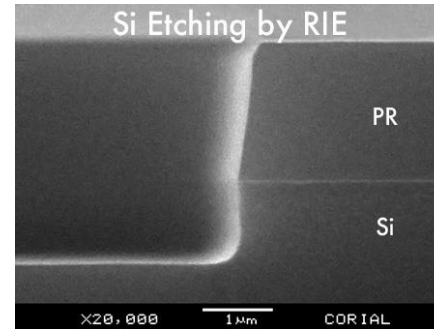
Fluorinated chemistry



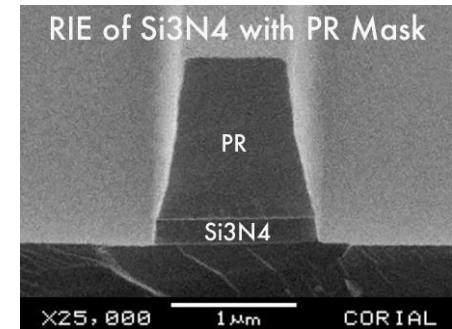
RIE of SiO₂ with PR mask –
Vertical profile – High etch
uniformity



RIE of SiO₂ with PR mask – 0.8 µm
deep



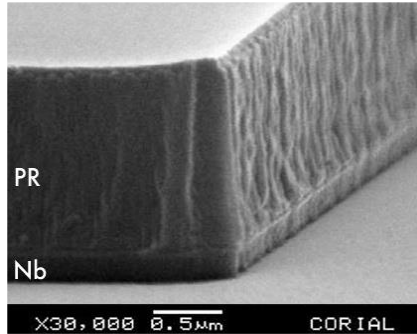
RIE of Si – 0.8 µm deep -
Anisotropic profile



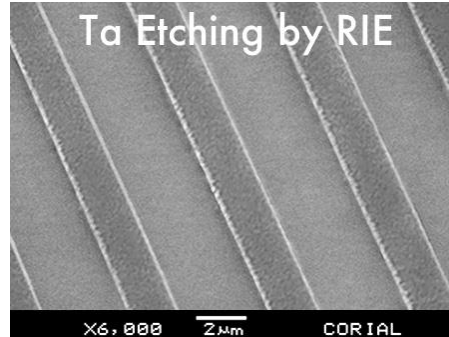
RIE of Si₃N₄ - 0.8 µm deep



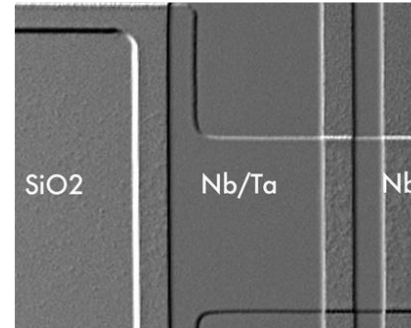
Fluorinated chemistry



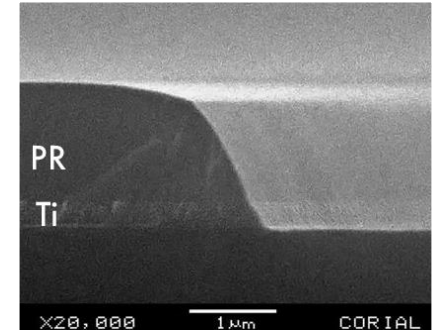
Nb etching with PR mask –
Anisotropic profile



Ta etching with PR mask –
Anisotropic profile



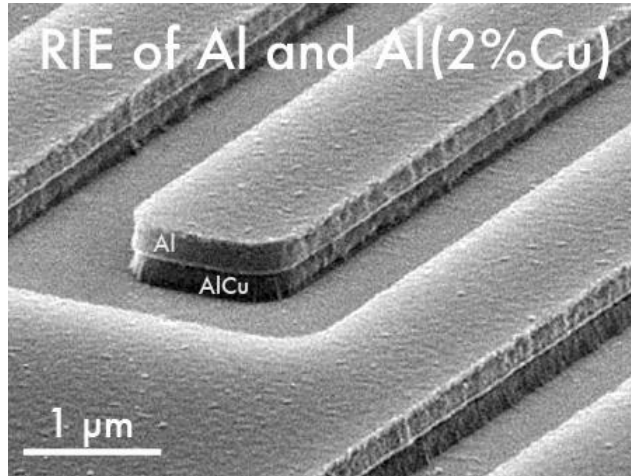
RIE of Nb / Ta



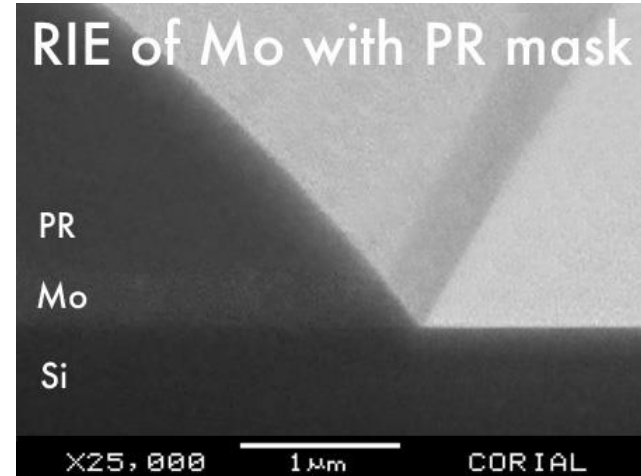
Ti etching with PR mask -
Anisotropic profile



Chlorinated chemistry



AlCu Etching with PR mask – Selective process

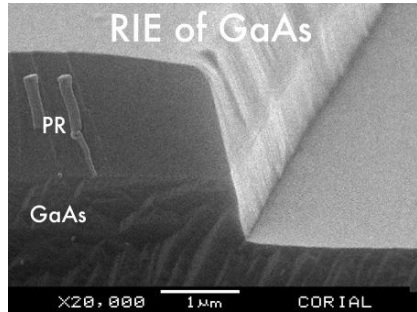


Mo Etching with PR mask

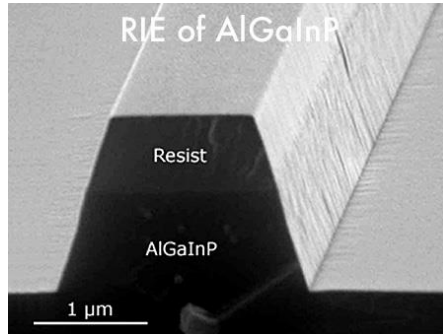


RIE OF III-V COMPOUNDS

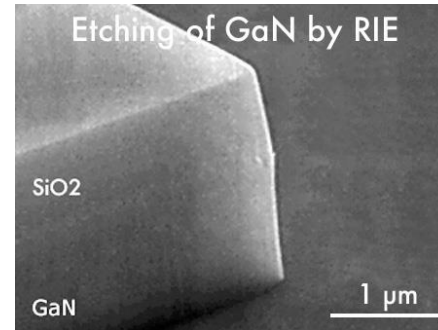
9/5/2018



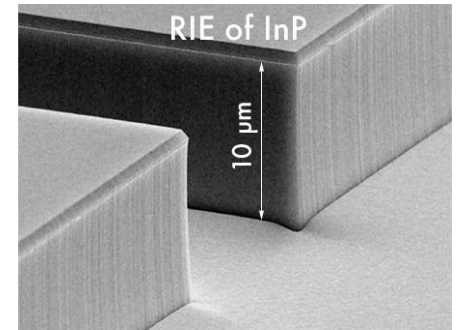
RIE of GaAs – High etch rate –
High selectivity



RIE of AlGaInP – PR mask



RIE of GaN – SiO₂ mask



RIE of InP – High etch rate



HIGH ETCH RATES

9/5/2018

Excellent Uniformities

Process	Mask	Etch rate (nm/min)	Selectivity (vs mask)	Uniformity (across wafer)
Polymers	PR	400	1	±5%
SiO ₂	PR	45	> 2	±3%
Si ₃ N ₄	PR	60	> 2	±3%
InP	SiO ₂	80	> 50	±3%
GaN	SiO ₂	200	5	±5%
GaAs	PR	300	6	±5%
Al	PR	180	1	±5%
Ta	PR	90	> 0.5	±5%
Ti	PR	25	0.3	±5%
Nb	PR	110	> 0.5	±5%

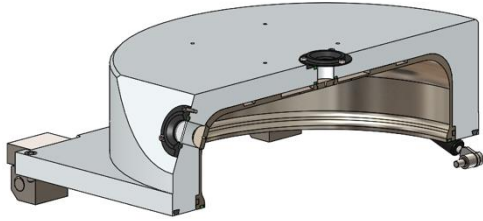
RIE SOURCE FOR SPUTTER-ETCH **CORIAL 210RL**



SPUTTER ETCH

9/5/2018

RIE process chamber for etching and sputtering

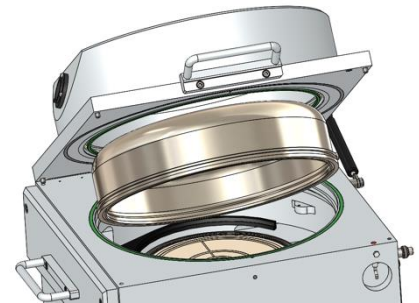
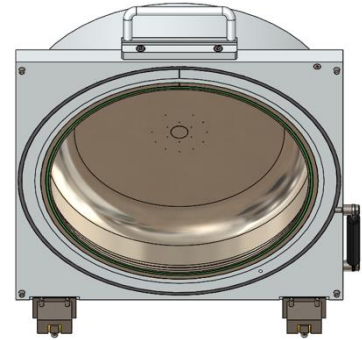


LINER TO COLLECT
ETCH-BY-PRODUCTS
AND SPUTTERED
MATERIALS

Dedicated process
chamber for
Au, Ag, Ni, Fe, Co,
Pt, PZT...
SPUTTERING

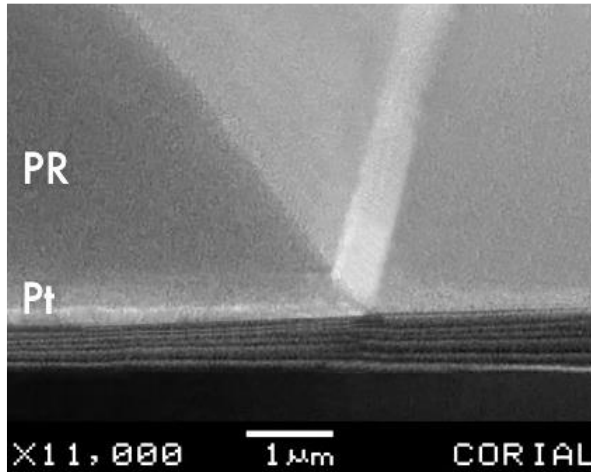


EASY LINER
replacement by
a single person





Ar chemistry



Process	Mask	Etch rate (nm/min)	Selectivity (vs mask)	Uniformity (across wafer)
Au, Pt, PZT, Fe, Co	PR	45	> 1	±5%

Back sputtering of Pt with PR mask

SHUTTLE HOLDING APPROACH CORIAL 210RL



SHUTTLE HOLDING APPROACH

9/5/2018

Portfolio

NG20 wafer carrier

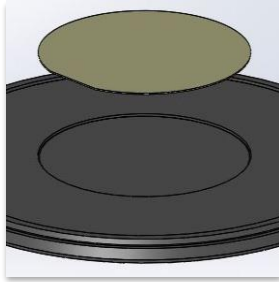
50 mm wafer



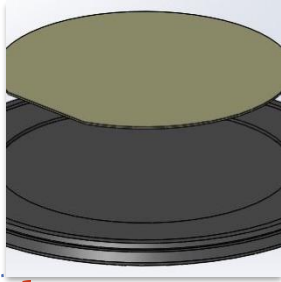
75 mm wafer



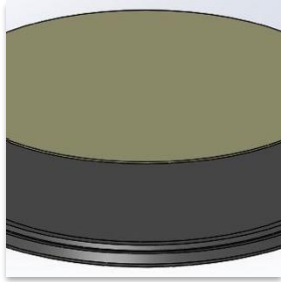
100 mm wafer



150 mm wafer

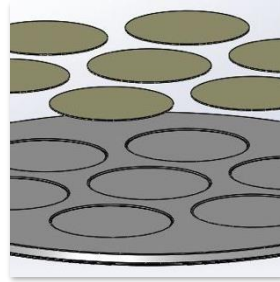


200 mm wafer

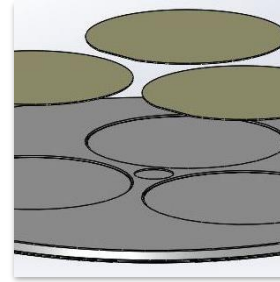


NQ200 wafer carrier

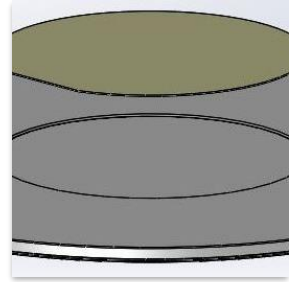
50 mm wafer



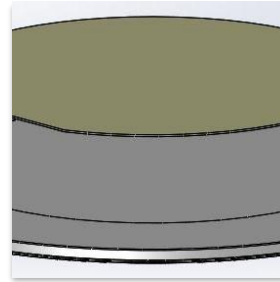
75 mm wafer



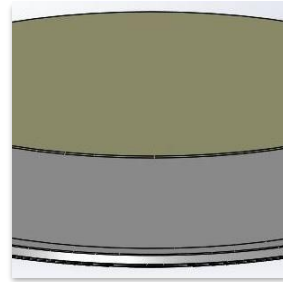
100 mm wafer



150 mm wafer



200 mm wafer



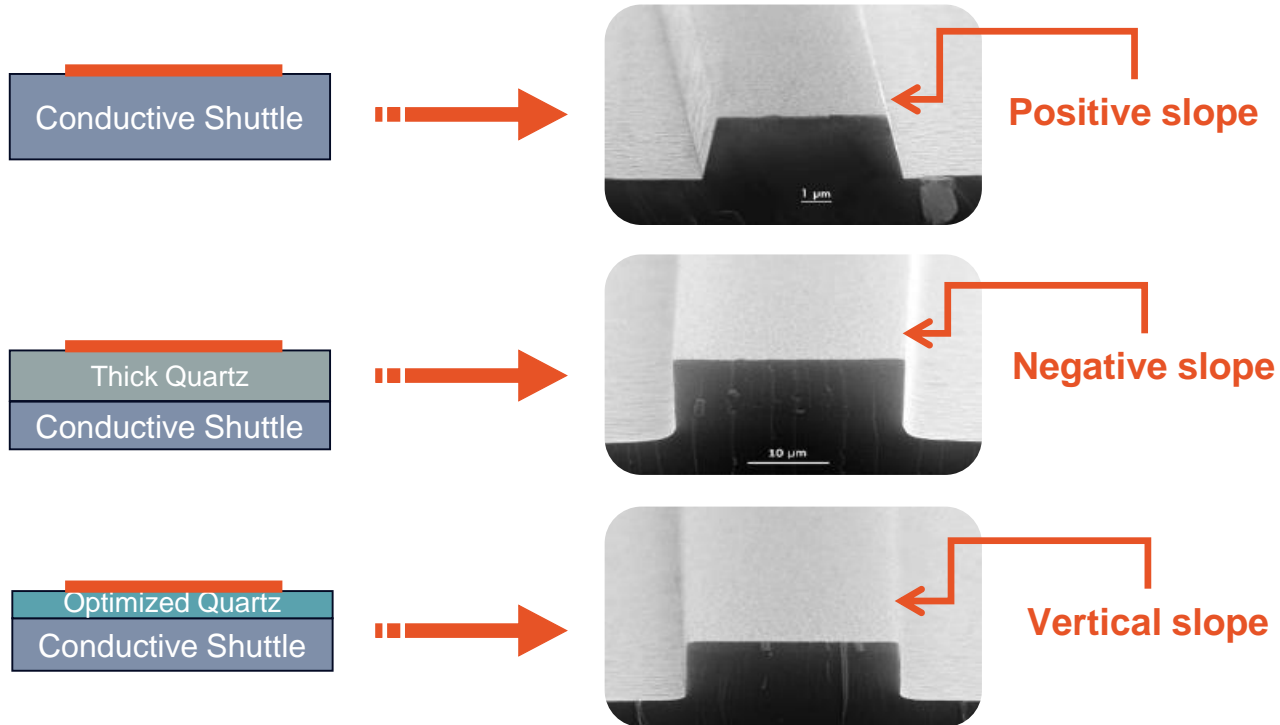


SHUTTLE HOLDING APPROACH

9/5/2018

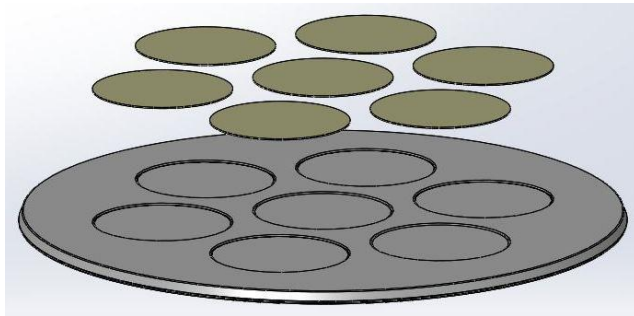
Impact on Performances

SiO₂ etching with aSi-H mask



SHUTTLE HOLDING APPROACH

Benefits



1. Quick adaptation to sample shape and size
2. Optimum process conditions with NO modification of process chamber
3. Limited cross contamination between processes by using dedicated shuttles

2''

Wafer carrier

USABILITY

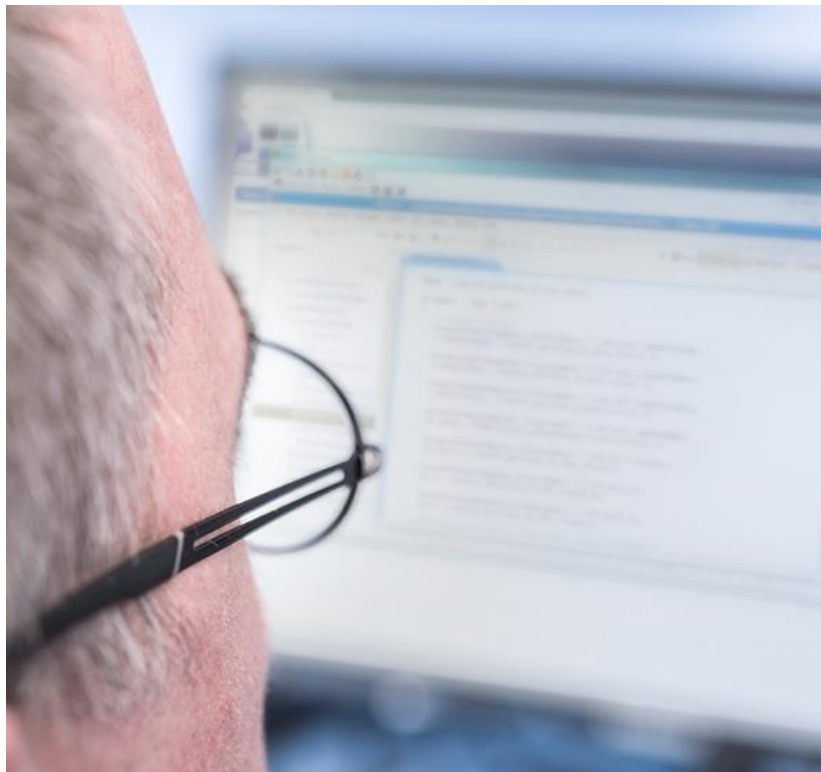
CORIAL 210RL



PROCESS CONTROL SOFTWARE

9/5/2018

COSMA



COSMA

CORIAL OPERATING SYSTEM FOR MACHINE

The simplest, most efficient software to develop processes, operate, and maintain CORIAL systems



DESKTOP APPLICATION

Process Editing | Process Adjustment | Process Operation | Process Tracability | System Maintenance



REMOTE CONTROL





REPROCESSING SOFTWARE

9/5/2018

COSMA RS



DISPLAY UP TO
4
PARAMETERS
FROM A RUN

Simple and efficient
software to analyze process
runs and accelerate process
development

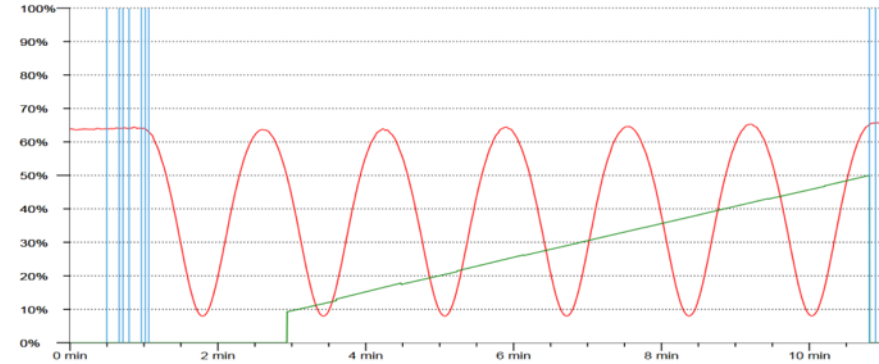
REMOTE
ANALYSIS OF RUNS

DRAG AND DROP
CURVES TO CHECK PROCESS
REPEATABILITY



END POINT DETECTION

9/5/2018



A CCD camera and laser diode, in the same measuring head, enables simultaneous visualization of the wafer surface and the laser beam impact on it. A 20 μm diameter laser spot facilitates the record of interference signals.

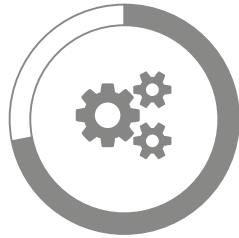
Real-Time etch rate measurement
Real-Time etched depth
measurement



Anisotropic RIE etching supported by a wide range of processes



RIE capabilities over a variety of materials including Silicon compounds, metals, polymers, III-V and II-VI compounds



Modular design approach supporting tiered upgrades



Smaller wafer pieces up to full 200 mm wafer
1x2" to 7x2" ; 1x3" to 3x3" ; 1x4" ; 1x6" ; 1x8"

